MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

RCLAMP3324P

Product specification





FEATURES

- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.25pF typ. IO-IO)
- IEC 61000-4-2

±20kV (contact

discharge) ±20kV

(air discharge)

• IEC 61000-4-4 (EFT) 40A (5/50ns)

APPLICATIONS

- USB2.0, USB3.0 interface
- HDMI1.3,HDMI1.4 and HDMI2.0
- industrial equipment
- Digital Visual Interface
- Notebools

Reference News

PACKAGE OUTLINE	PIN CONFIGURATION	Marking
A STATE	Pin 1 Pin 2 Pin 4 Pin 5 Pin 3, 8	3324P XXXX
DFN-10		

- Tiny DFN-10(2.5mmx1.0mm) package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant



ABSOLUTE MAXIMUM RATING

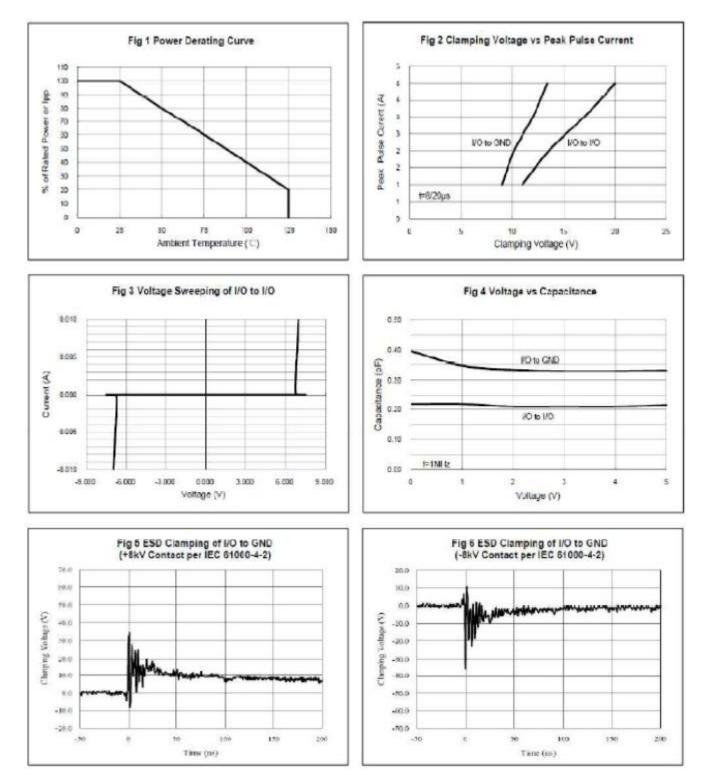
Symbol	Parameter	Value	Units	
	ESD per IEC 61000-4-2 (Contact)	±20		
VESD	ESD per IEC 61000-4-2 (Air)	±20	kV	
PPP	Peak Pulse Power (8/20µs)	60	W	
ТОРТ	Operating Temperature	-55~125	°C	
TSTG	Storage Temperature	-55~150	°C	

ELECTRICAL CHARACTERISTICS (Tamb=25 °C)

Symbol	Parameter	Test Condition	Min	Тур	Max	Units
	Reverse Working Voltage				3.3	V
VBR	Reverse Breakdown Voltage	IT = 1mA	4.2			V
IR	Reverse Leakage Current	V _{RWM} =3.3V,T=25C			100	nA
VC	Clamping Voltage	IPP = 4A, tp = 8/20µs			15	V
CJ	Junction Capacitance	VR = 0V, f = 1MHz IO to IO		0.25	0.4	pF
		VR = 0V, f = 1MHz IO to Gnd		0.4	0.6	pF

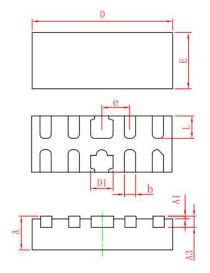


ELECTRICAL CHARACTERISTICS CURVE





PACKAGE MECHANICAL DATA



Cumbel	Dimens	sions in millir	neters
Symbol	Min	Nom	Max
A	0.45	0.50	0.55
A1	-	0.02	0.05
A3	0.10	0.15	0.20
D	2.45	2.50	2.55
E	0.95	1.00	1.05
D1	0.35	0.40	0.45
b	0.15	0.20	0.25
е		0.50BSC	1/1
L	0.35	0.40	0.45

REEL SPECIFICATION

P/N	PKG	QTY
RCLAMP3324P	DFN-10	3000



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